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ED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

Jun Kanamori

Group Art Unit: 2814

Serial No:: 09/398,189

Examiner: S. Rao

Filed: September 17, 1999

METHOD OF FABRICATING A SEMICONDUCTOR DEVICE WITH SELF-

ALIGNED SILICIDE AREAS FORMED USING A SUPPLEMENTAL SILICON

OVERLAYER

<u>AMENDMENT</u>

Honorable Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

Date: February 4, 2002 (Monday)

In response to the Office Action dated October 2, 2001, the period for response having been extended one (1) month to February 2, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

In the Claims:

Please cancel claims 1,7-9 and 19-22 without prejudice or disclaimer of the subject matter contained therein.

The following replacement claims are respectfully submitted:

(Twice Amended) The method according to claim 23, wherein the metal layer comprises cobalt (Co